

## P-Channel Enhancement Mode Power MOSFET

### DESCRIPTION

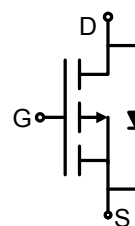
The HM15P06Q uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 4.5V.

### GENERAL FEATURES

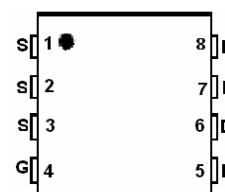
- $V_{DS} = -60V, I_D = -15A$   
 $R_{DS(ON)} < 60m\Omega @ V_{GS} = -4.5V$   
 $R_{DS(ON)} < 45m\Omega @ V_{GS} = -10V$
- High Power and current handing capability
- Lead free product is acquired
- Surface Mount Package

### Application

- Battery Switch
- Load switch
- Power management



Schematic diagram



Marking and pin assignment

### Package Marking And Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
HM15P06Q	HM15P06Q	DFN3X3-8L	Ø330mm	12mm	2500 units

### Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	-60	V
Gate-Source Voltage	$V_{GS}$	±20	V
Drain Current-Continuous	$I_D$	-15	A
Drain Current-Pulsed (Note 1)	$I_{DM}$	-45	A
Maximum Power Dissipation	$P_D$	50	W
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	°C

### Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	40	°C/W
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### Electrical Characteristics (TA=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-60	-33	-	V

Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-60V, V <sub>GS</sub> =0V	-	-	-1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250μA	-1.2	-	-2.5	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-10A	-	-	45	mΩ
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-7.0A	-	-	60	mΩ
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =-15V, I <sub>D</sub> =-9.1A	10	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =-15V, V <sub>GS</sub> =0V, F=1.0MHz	-	1600	-	PF
Output Capacitance	C <sub>oss</sub>		-	350	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>		-	300	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =-15V, I <sub>D</sub> =-1A, V <sub>GS</sub> =-10V, R <sub>GEN</sub> =6Ω	-	10	-	nS
Turn-on Rise Time	t <sub>r</sub>		-	15	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>		-	110	-	nS
Turn-Off Fall Time	t <sub>f</sub>			70	-	nS
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =-15V, I <sub>D</sub> =-9.1A V <sub>GS</sub> =-10V	-	30	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	5.5	-	nC
Gate-Drain Charge	Q <sub>gd</sub>		-	8	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =-2.1A	-	-	-1.2	V

### Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

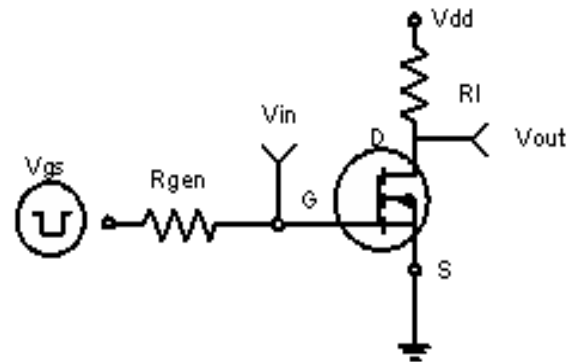


Figure 1: Switching Test Circuit

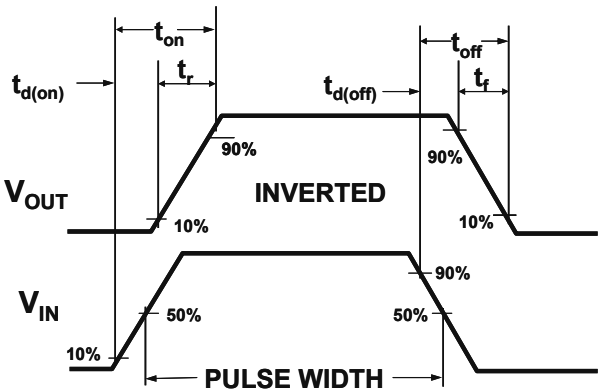


Figure 2: Switching Waveforms

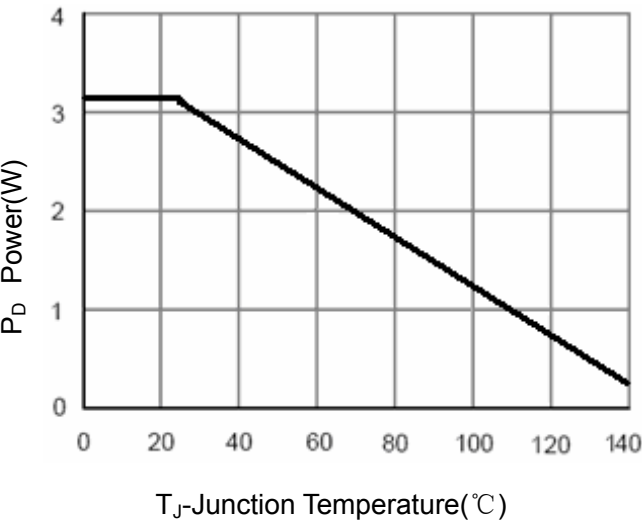


Figure 3 Power Dissipation

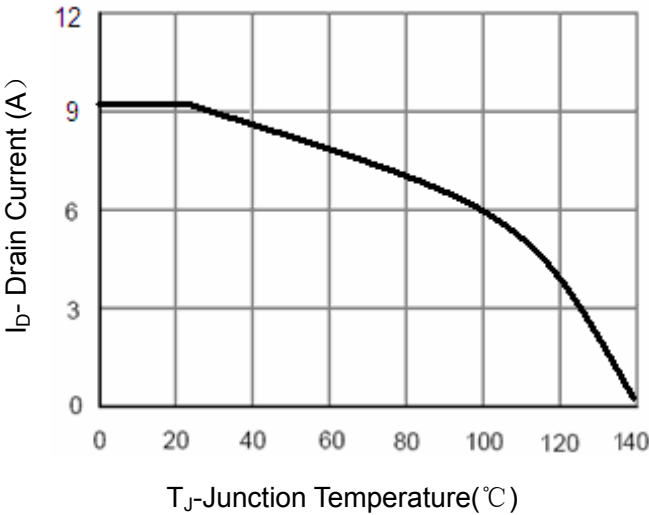


Figure 4 Drain Current

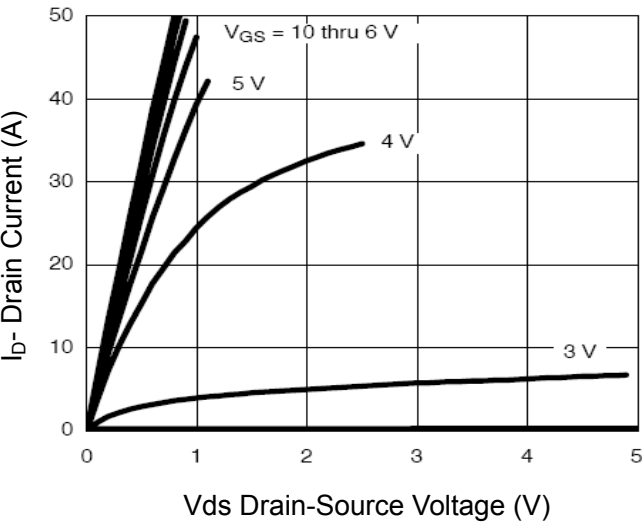


Figure 5 Output CHARACTERISTICS

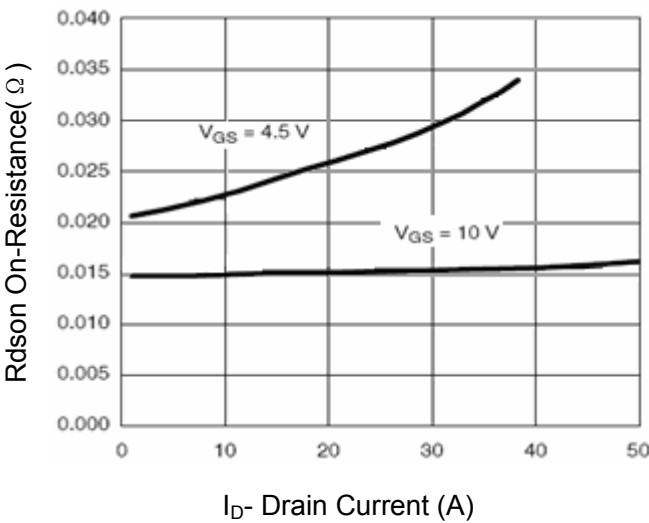
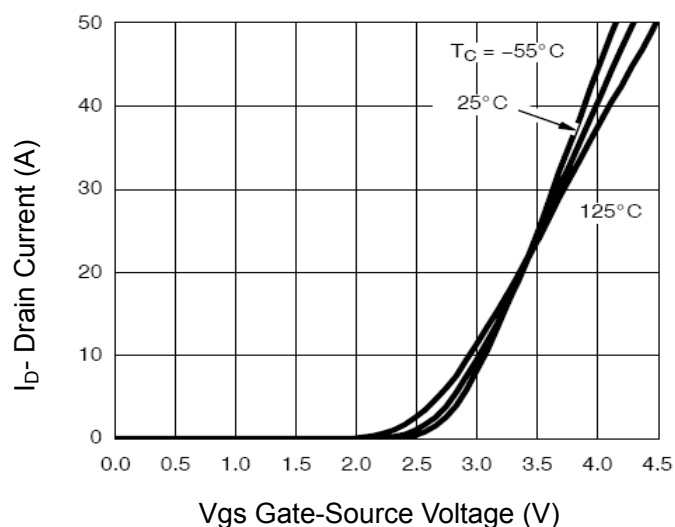
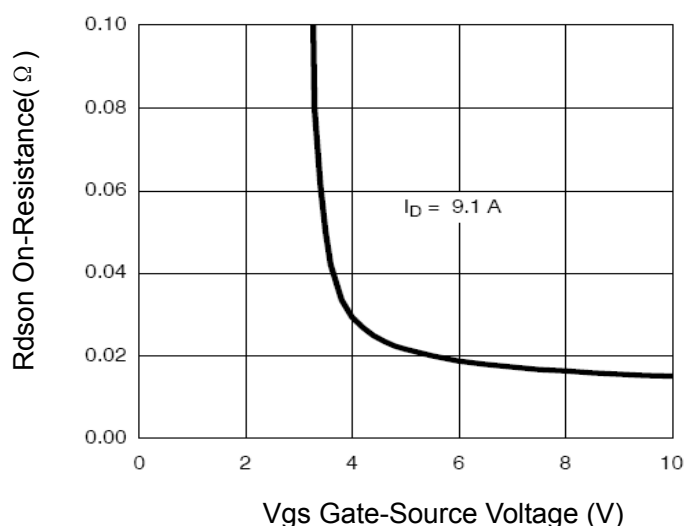


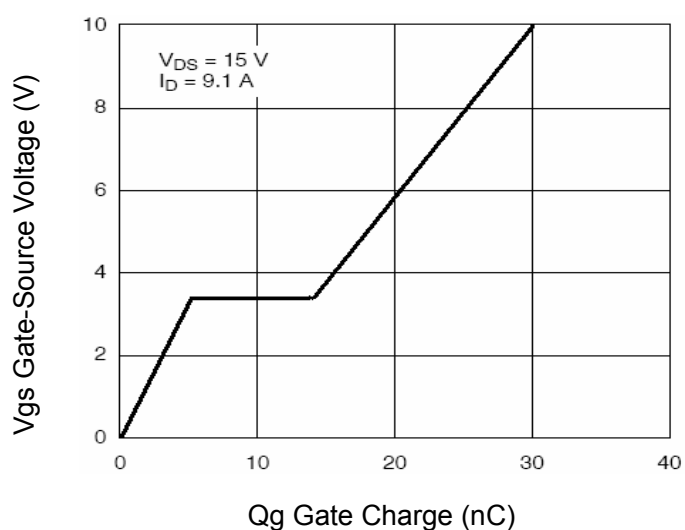
Figure 6 Drain-Source On-Resistance



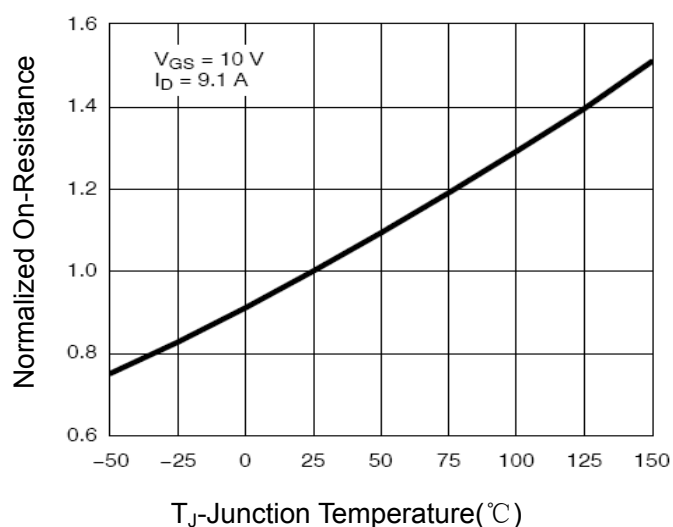
**Figure 7 Transfer Characteristics**



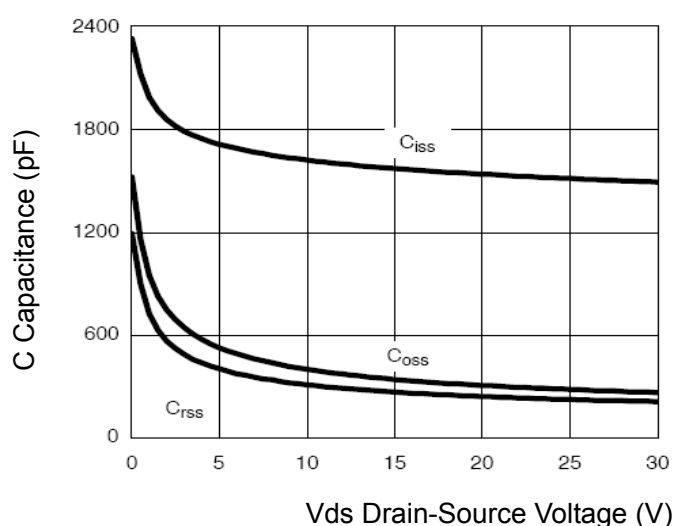
**Figure 9 Rdson vs Vgs**



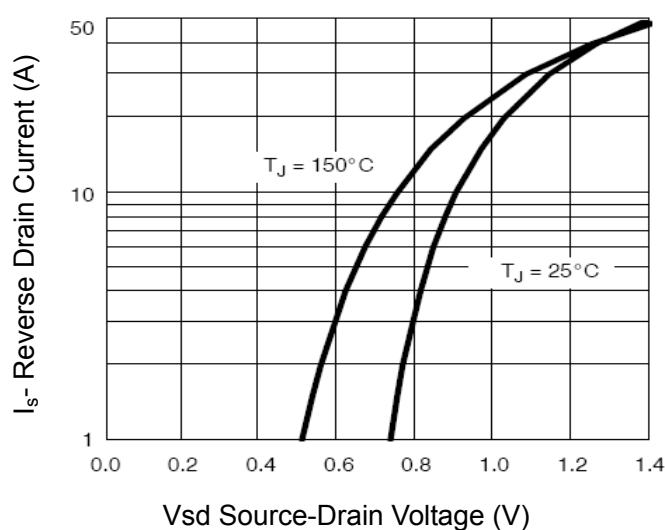
**Figure 11 Gate Charge**



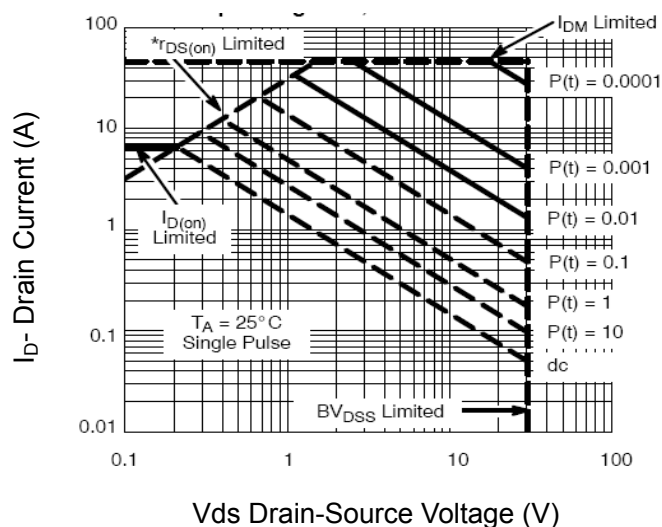
**Figure 8 Drain-Source On-Resistance**



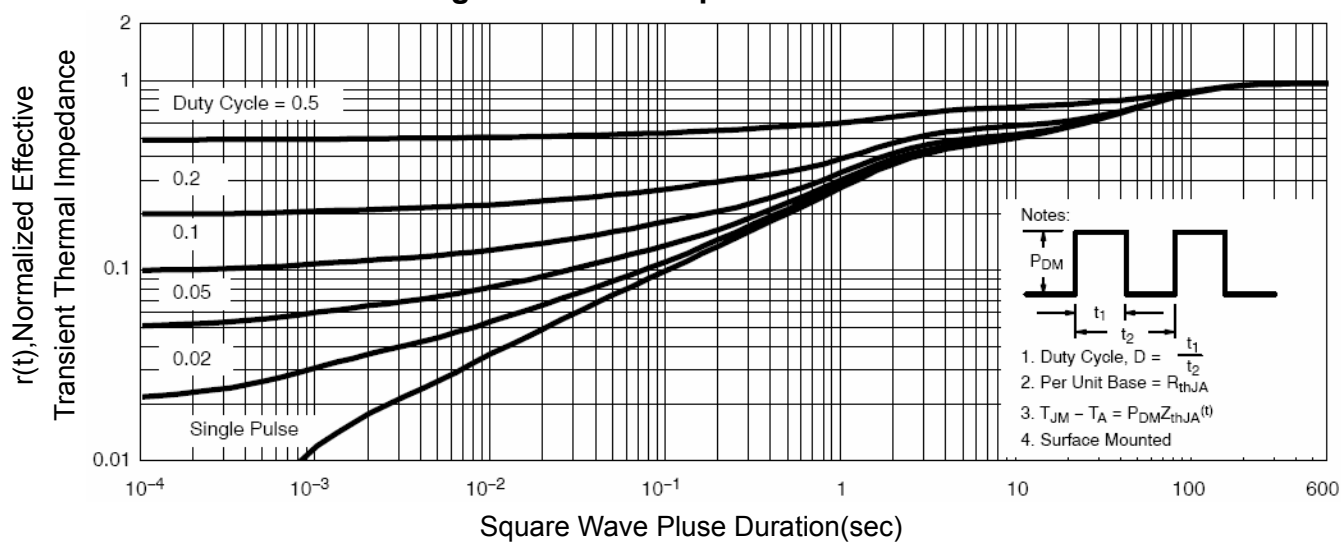
**Figure 10 Capacitance vs Vds**



**Figure 12 Source- Drain Diode Forward**

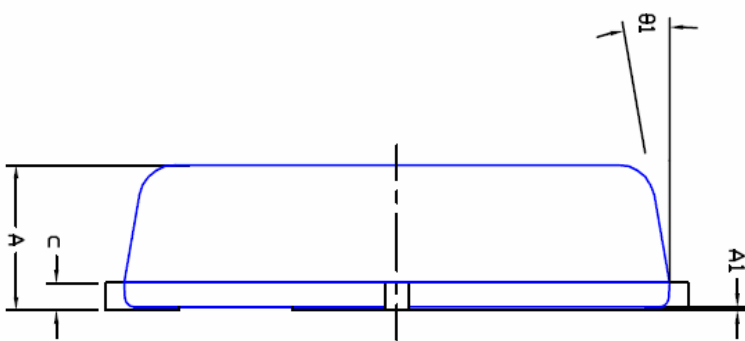
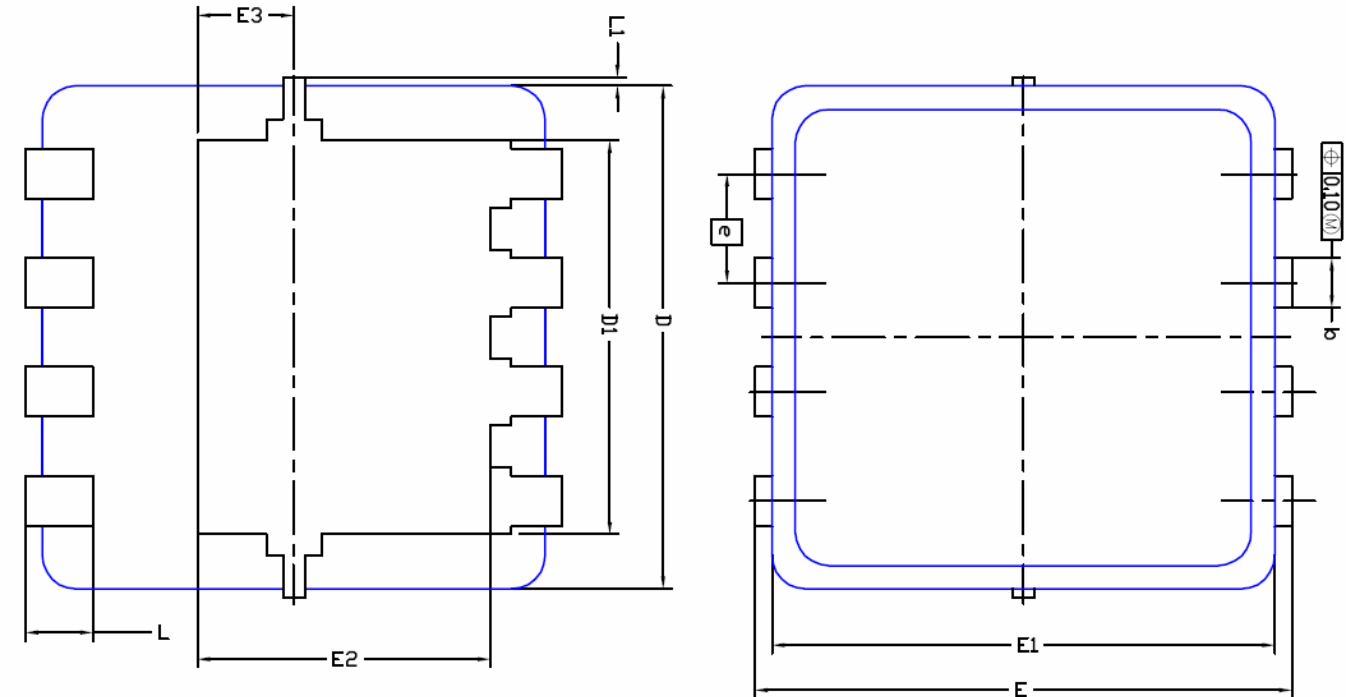


**Figure 13 Safe Operation Area**



**Figure 14 Normalized Maximum Transient Thermal Impedance**

DFN3X3 EP Package Information



DIM.	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.700	0.80	0.900	0.0276	0.0315	0.0354
A1	0.00	---	0.05	0.000	---	0.002
b	0.24	0.30	0.35	0.009	0.012	0.014
c	0.10	0.152	0.25	0.004	0.006	0.010
D	3.00 BSC			0.118 BSC		
D1	2.35 BSC			0.093 BSC		
E	3.20 BSC			0.126 BSC		
E1	3.00 BSC			0.118 BSC		
E2	1.75 BSC			0.069 BSC		
E3	0.575 BSC			0.023 BSC		
e	0.65 BSC			0.026 BSC		
L	0.30	0.40	0.50	0.0118	0.0157	0.0197
L1	0	---	0.100	0	---	0.004
θ1	0°	10°	12°	0°	10°	12°